

Properties of REAlB₄ and Lu₂AlB₆ crystals grown from RE–Al–B (RE = Tm, Yb, Lu) melts

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Abstract

Crystals of TmAlB₄, YbAlB₄, LuAlB₄ and Lu₂AlB₆ were grown using RE₂O₃ (RE = Tm, Yb, Lu) and crystalline boron as starting materials in a self-component aluminum solution under an argon atmosphere at 1773 K for 10 h. REAlB₄ (RE = Tm, Yb, Lu) and Lu₂AlB₆ crystals were generally obtained in the form of prismatic shape extending in the *c* direction and with well-developed {001} or {100} planes. REAlB₄ and Lu₂AlB₄ crystals have the maximum size of approximately 3.5 mm. The as-grown crystals were measured for the Vickers microhardness at room temperature and magnetic susceptibility at low temperatures (2–300 K). The values of the Vickers microhardness for REAlB₄ and Lu₂AlB₆ in several directions on {001} and {100} planes were in the range of 14.0 ± 0.6 to 14.5 ± 1.4 and 18.9 ± 0.7 GPa, respectively. The magnetic susceptibility of REAlB₄ (RE = Yb, Lu) and Lu₂AlB₆ increases paramagnetically as temperature is lowered. Superconductivity was not observed in any of the samples down to a temperature of 2 K. An antiferromagnetic transition was found in TmAlB₄ with Neel transition temperature of *T*_N = 5.5 K.

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1. Introduction

Three types of ternary compounds have been reported in RE–Al–B (RE = Tm, Yb, Lu) systems, namely RE₂AlB₆ (Y₂ReB₆-type, orthorhombic, space group *Pbam*), REAlB₄ (YCrB₄-type, orthorhombic, space group *Pbam*) and REAlB₁₄ (MgAlB₁₄-type, orthorhombic, space group *Imma*) [1–5]. RE₂AlB₆ and REAlB₄ crystals are of great interest because of their remarkable physical and chemical properties, which in many cases are of potential interest for applications to thermoelectric and photodetector materials [6]. However,

there is very little information about the physical and chemical properties of RE₂AlB₆ and REAlB₄ crystals. REAlB₄ has the same structure as that postulated for YCrB₄. The linkage of boron atoms in the structures of YCrB₄- and Y₂ReB₆-type differs according to the chemical composition as follows: in REAlB₄, the boron network is built up by five- and seven-membered rings, while in RE₂AlB₆, boron network consists of five-, six-, and seven-membered rings. The structures of REAlB₄ and RE₂AlB₆ are built up by two-dimensional boron networks sandwiched between metal layers. These boron atoms reside in the interstitial sites of trigonal prisms, formed by the RE (RE = Tm, Yb, Lu) and Al atoms. Using high-temperature syntheses Al-self components, crystal morphology, chemical analyses, and crystallographic data of the

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Table 1
Conditions for growth of REAlB₄ and Lu₂AlB₆ crystals from RE–Al–B (RE = Tm, Yb, Lu) melts

Compounds	Atomic ratios, B/RE = <i>n</i>
TmAlB ₄	2.0
YbAlB ₄	1.0 or 2.0
LuAlB ₄	5.5
Lu ₂ AlB ₆	3.0

as-grown crystals of REAlB₄ (RE = Tm, Yb, Lu) and Lu₂AlB₆ were reported previously [3–5]. Here we investigate Vickers microhardness at room temperature and magnetic susceptibility of these compounds at low temperatures.

2. Experimental

REAlB₄ (RE = Tm, Yb, Lu) and Lu₂AlB₆ crystals were prepared from RE₂O₃ powder (RE = Tm, Yb, Lu) (99.9% purity) (particle size 0.5 μm), crystalline boron powder (99% purity) (particle size 5–250 μm) and aluminum chips (99.99% purity). RE₂O₃ and B powders were weighed in with atomic ratios $n = B/RE = 1.0$ – 8.0 according to the reaction:



Al metal was added to each mixture at a mass ratio of 1: 15. From the above preliminary experimental results, the optimum growth conditions of REAlB₄ and Lu₂AlB₆ are shown in Table 1. The mixture of starting materials was placed in a high-density alumina (99.9% purity) crucible and heated under an Ar atmosphere. The temperature of the furnace was raised at a rate of 300 K h⁻¹ up to 1773 K and held for 10 h at that temperature, and then slowly cooled down at a rate of 50 K h⁻¹ to 1273 K. Subsequently the furnace was rapidly cooled down to room temperature. The crystals grown in this way were separated from the solidified melts by dissolving the excess Al with about 6 mol dm⁻³ hydrochloric acid.

REAlB₄ (RE = Tm, Yb, Lu) and Lu₂AlB₆ crystals were selected under a stereomicroscope for chemical analyses and measurements of Vickers microhardness and magnetic susceptibility at low temperatures.

Phase analysis and determination of unit-cell parameters were carried out using a powder X-ray diffractometer (XRD) (Rigaku, RU-200) with monochromatic Cu Kα radiation.

The morphological properties and impurities of the crystals were investigated by a scanning electron microscope (SEM) (JEOL, T-20) and an energy dispersive X-ray detector (EDX) (Horiba, EMAX-2770). The chemical compositions of the crystals grown were determined by means of the inductively coupled plasma (ICP) method (Shimadzu, ICP-50). The density of the crystals was measured using a pycnometer with distilled water at room temperature.

Measurements on as-grown REAlB₄ and Lu₂AlB₆ crystals were done using a Vickers diamond indenter at room temperature. A load of 0.98 N was applied for 15 s at about seven positions on relatively large {001} and {100} planes of each crystal, and the values obtained were averaged. Magnetic susceptibility of as-grown crystals was measured by using a superconducting quantum interference device (SQUID) magnetometer in the temperature range of 2–300 K.

3. Results and discussion

The atomic ratio B/RE in starting materials was varied from 1.0 to 8.0. The optimum growth conditions of REAlB₄ and Lu₂AlB₆ crystals are shown in Table 1. The variation of the atomic ratio B/RE of starting materials gave different compounds, and with increased boron concentration, more boron-rich aluminum borides (α-AlB₁₂ and β-AlB₁₂) [7,8] were obtained. However, REAlB₄ and Lu₂AlB₆ crystals were obtained as a phase mixture together with REB₄ (RE = Tm or Yb or Lu) or YbB₆ crystals. REAlB₄ and Lu₂AlB₆ crystals were generally obtained in the form of prismatic shape extending in the *c* direction (Fig. 1) and with well-developed {001} or {100} planes. The largest crystals have the maximum sizes of approximately 0.2 mm × 3.2 mm × 3.5 mm for REAlB₄ and approximately 0.2 mm × 0.3 mm × 3.5 mm for Lu₂AlB₆, respectively.

The basic crystal data and chemical compositions of REAlB₄ and RE₂AlB₆ crystals are listed in Table 2. The well characterized ternary metal boride TmAlB₄ and Lu₂AlB₆ have so far not been reported. The diffraction data for TmAlB₄ is very similar to those reported for YbAlB₄ ($a = 0.5927(2)$ nm, $b = 1.147(1)$ nm, $c = 0.3492(1)$ nm) and LuAlB₄ ($a = 0.5906(2)$ nm, $b = 1.144(1)$ nm and $c = 0.3480(1)$ nm) [2]. The X-ray diffraction data for Lu₂AlB₆ are very similar to those reported for Yb₂AlB₆

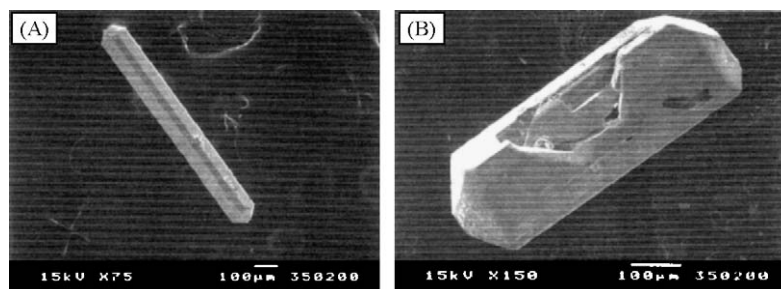


Fig. 1. SEM photographs of TmAlB₄ (A) and Lu₂AlB₆ (B) crystals.

Table 2
Crystal data and chemical analyses of REAlB₄ (RE = Tm, Yb, Lu) and Lu₂AlB₆ crystals

Formula	TmAlB ₄	YbAlB ₄	LuAlB ₄	Lu ₂ AlB ₆
Crystal system	Orthorhombic	Orthorhombic	Orthorhombic	Orthorhombic
<i>a</i> (nm)	0.5918(1)	0.5919(1)	0.5898(1)	0.8987(1)
<i>b</i> (nm)	1.1472(1)	1.1465(2)	1.1420(1)	1.1334(1)
<i>c</i> (nm)	0.3477(1)	0.3492(1)	0.3485(1)	0.3633(1)
<i>V</i> (nm ³)	0.2361(1)	0.2369(1)	0.2347(1)	0.3701(1)
Space group	<i>Pbam</i>	<i>Pbam</i>	<i>Pbam</i>	<i>Pbam</i>
<i>d_m</i> (g cm ⁻³)	6.69(4)	6.78(5)	6.90(4)	7.88(6)
<i>d_x</i> (g cm ⁻³)	6.729(2)	6.821(3)	6.939(6)	7.930(5)
<i>Z</i>	4	4	4	4
RE (mass%)	70.9	70.8	71.1	79.2
Al (mass%)	10.2	10.6	17.1	14.5
B (mass%)	17.0	17.6	10.0	5.7
Total (mass%)	98.1	99.0	98.2	99.4
Chemical composition	TmAl _{0.9} B _{3.8}	YbAl _{1.0} B _{4.0}	LuAl _{0.9} B _{3.9}	Lu ₂ Al _{0.9} B _{5.9}

(*a* = 0.9127(5) nm, *b* = 1.146(1) nm, *c* = 0.3584(4) nm) [9].

The results of the Vickers microhardness for as-grown REAlB₄ and RE₂AlB₆ crystals are listed in Table 3. The microhardness values on the {001} planes of REAlB₄ crystals were in the range of 14.0 ± 0.6 to 14.5 ± 1.4 GPa. The microhardness values of REAlB₄ crystals were found to be closely similar. The hardness value of Lu₂AlB₆ crystal is relatively higher than the values for REAlB₄ and 12.7 ± 0.8 GPa for Sc₂AlB₆ in the literature [10]. The linkage of boron atoms in the structures of YCrB₄ and Y₂ReB₆-types [9] differs according to the chemical composition. The structure of YCrB₄ has boron networks built up by five- and seven-membered rings, and for Y₂ReB₆ has boron networks consisting of five-, six-, and seven-membered rings. Considering the significant difference in structure, especially from Lu₂AlB₆, the difference in the hardness of the aluminum–lutetium boride compounds is noteworthy.

Recently interesting magnetic behavior has been found in boron-rich compounds such as REB₅₀ [11] and REB₂₂C₂N [12]. It is interesting to investigate the magnetic properties of the new boron-rich system REAlB₄ since the properties are completely unknown to date. It is also important to check for the presence of superconductivity. The magnetic susceptibility of YbAlB₄ is shown in Fig. 2. As temperature is lowered, the susceptibility increases paramagnetically, but no large anomalies. A magnetic transition is observed down to 2 K. A small hump below 20 K indicates that a small amount of a kind of ferromagnetic impurity phase exists in the YbAlB₄ samples. It is not clear exactly what this phase is at present.

Table 3
Vickers microhardness of REAlB₄ and Lu₂AlB₆ crystals

Compounds	Load (N)	Vickers microhardness (GPa)
TmAlB ₄	0.98	14.5 ± 1.4
YbAlB ₄	0.98	14.2 ± 1.4
LuAlB ₄	0.98	14.0 ± 0.6
Lu ₂ AlB ₆	0.98	18.9 ± 0.7

Load time: 15 s.

The magnetic susceptibility of TmAlB₄ is shown in Fig. 3. Similar to YbAlB₄, the susceptibility increases paramagnetically as temperature is lowered, but a large drop in the susceptibility is observed at low temperatures indicating that an antiferromagnetic transition has occurred. The transition temperature is determined to be *T_N* = 5.5 K. This is the first magnetic transition observed in this series of samples, and the

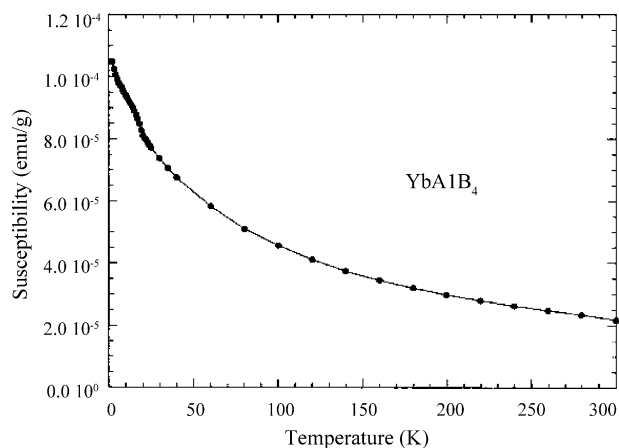


Fig. 2. Temperature dependence of the magnetic susceptibility of YbAlB₄.

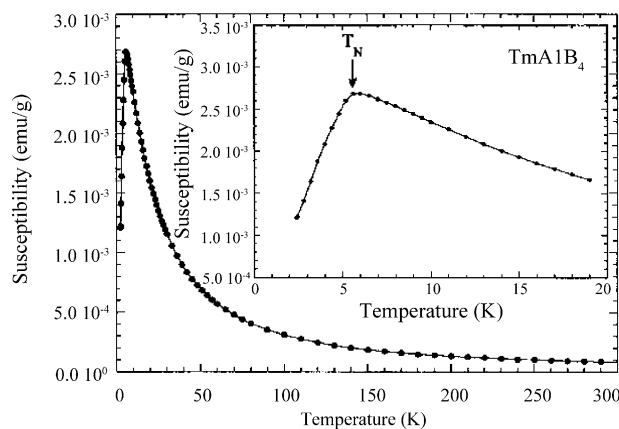


Fig. 3. Temperature dependence of the magnetic susceptibility of TmAlB₄.

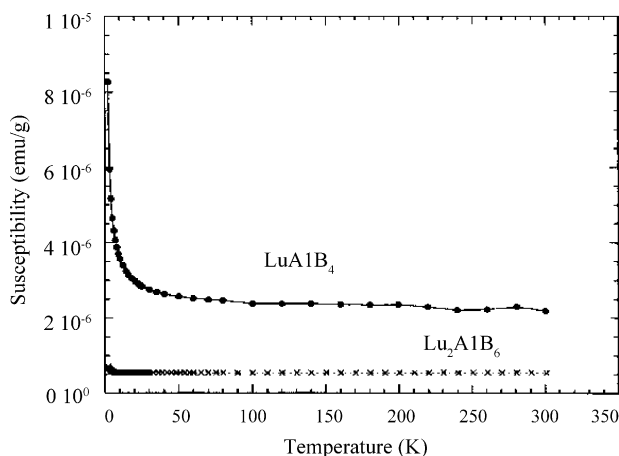


Fig. 4. Temperature dependence of the magnetic susceptibility of Lu_2AlB_6 and LuAlB_4 .

transition temperature range appears to be similar to what has been observed for other boron-rich borides [12].

Although LuAlB_4 and Lu_2AlB_6 do not contain atoms with large magnetic spin, it is interesting to investigate the magnetic properties of these new boron-rich compounds since the properties are completely unknown to date. It is also important to check for the presence of superconductivity. The magnetic susceptibilities of LuAlB_4 and Lu_2AlB_6 are shown in Fig. 4. LuAlB_4 shows little temperature dependence and appears to be dominated by Pauli paramagnetic susceptibility of metals. The magnetic susceptibility takes a value of 2.2×10^{-6} emu/g at 300 K. The increase at low temperatures is indicative of a minor contribution, which we attribute to impurities. The impurity component of LuAlB_4 appears to be larger than that of Lu_2AlB_6 .

Superconductivity does not exist in REAlB_4 (RE = Tm, Yb, Lu) and Lu_2AlB_6 compounds down to a temperature of 2 K.

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